FM30H100Q/M

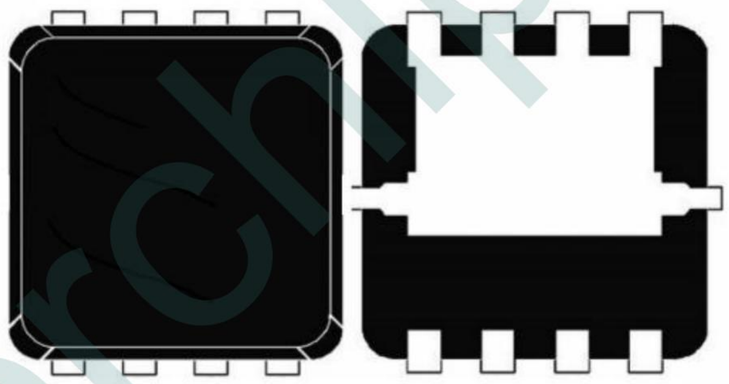
N-Channel Trench Power MOSFET

- 30V,100A
- $R_{DS(ON)}$=3.3mΩ (Typ.) @ V_{GS} =10V
- $R_{DS(ON)}$=5.8mΩ (Typ.) @ V_{GS} =4.5V
- Advanced Trench Technology
- Provide Excellent RDS(ON) and Low Gate Charge
- Lead free product is acquired

Application

- Load Switch
- PWM Application
- Power management

Package



PDFN-8 3*3(DPAK) view

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	100	A
		T_C = 100℃	32	A
I_{DM}	Pulsed Drain Current note1		360	A
E_{AS}	Single Pulsed Avalanche Energy note2		225	mJ
P_D	Power Dissipation	T_C = 25℃	45	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.78	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-50 to +150	℃

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